

### SPECIFICATION AMENDMENTS

Please replace paragraph [0048] with the following paragraph:

[0051] P+ polysilicon formed according to the present invention could be advantageously used in monolithic three dimensional memories such as those described in Johnson et al., US Patent No. 6,034,882, "Vertically stacked field programmable nonvolatile memory and method of fabrication"; Johnson, US Patent No. 6,525,953, "Vertically stacked field programmable nonvolatile memory and method of fabrication"; Knall et al., US Patent No. 6,420,215, "Three Dimensional Memory Array and Method of Fabrication"; Lee et al., US Patent Application No. 09/927648, "Dense Arrays and Charge Storage Devices, and Methods for Making Same," filed August 13, 2001 and assigned to the assignee of the present invention; and Herner et al., US Patent Application No. 10/326470, "An Improved Method for Making High-Density Nonvolatile Memory," filed December 19, 2002, assigned to the assignee of the present invention, all hereby incorporated by reference. P+ polysilicon formed according to the present invention can be used whenever P+ or doped polysilicon is called for in any of the patents or applications name herein.

Please replace paragraph [0051] with the following paragraph:

[0051] In one example, P+ polysilicon according to the present invention was formed on silicon wafers in an ASML RVP 9000. The ASML RVP 9000 has a capacity of 176 wafers. Every other slot was filled, so 88 wafers were used at an effective pitch of 8.6 mm. Of these 88 wafers, only 75 were product wafers, centered vertically; the rest were dummy wafers. The product wafers had previously had a layer of oxide deposited on them, and P+ polysilicon was deposited on the oxide. The remainder of the wafers were dummy wafers coated with a protective silicon nitride film to prevent breakage, as described in Herner et al., "Dummy Wafers and Methods for Making the Same," US Patent Application No. 10/036291, filed November 7, 2001, assigned to the assignee of the present invention, hereby incorporated by reference. The pressure was stabilized at 400 mTorr and the temperature at 460 degrees C. SiH<sub>4</sub> was flowed at 500 sccm, helium

was flowed at 700 sccm, and 1.5 percent  $\text{BCl}_3$  (balance helium) was flowed at 10 sccm to deposit 2000 angstroms of P+ polysilicon.

**AMENDMENTS TO THE SPECIFICATION: DISCUSSION**

The Examiner objected that the incorporation by reference of applications 09/927648 and 10/326470 in paragraph [0048] and of application 10/036291 in paragraph [0051] failed to recite that these applications are assigned to the assignee of the present invention. These paragraphs have been amended accordingly. These changes do not constitute new matter.